

ABSTRACT OF THE DISCLOSURE

Disclosed is a method for manufacturing a semiconductor laser device, comprising the steps of: (a) forming a first conductive-type clad layer, an active layer, and a second conductive-type clad layer on a first conductive-type semiconductor substrate; (b) forming a ridge structure by selectively etching the second conductive-type clad layer; (c) forming a current blocking layer around the ridge structure, the current blocking layer having protrusions on the upper surface thereof adjacent to the ridge structure, and an amorphous and/or polycrystalline layer on a partial area thereof; and (d) removing at least the amorphous and/or polycrystalline layer from the current blocking layer, and wet-etching the upper surface of the current blocking layer so that the protrusions are reduced in size;